

Attorney docket KAW 104

IN THE CLAIMS

1. (canceled)

2. (currently amended): ~~The semiconductor light emitting device according to claim 1;~~

A semiconductor light emitting device, comprising:

a semiconductor substrate;

a light emitting layer forming portion provided on said semiconductor substrate, in which an active layer made of a compound semiconductor is sandwiched between a first clad layer and a second clad layer made of compound semiconductor having band gap greater than that of said active layer, respectively and having a different conductivity type each other; and

a window layer provided at least above said second clad layer,

wherein said second clad layer is made of a compound semiconductor having a refractive index greater than that of said first clad layer provided on said semiconductor substrate side, and

wherein said window layer is made of a compound semiconductor having a refractive index greater than that of said second clad layer.

3. (currently amended): The semiconductor light emitting device according to claim [[1,]]

2, wherein the refractive index of said second clad layer is greater than the refractive index of said first clad layer by 6% to 4%.

4. (currently amended): The semiconductor light emitting device according to claim

[[1,]] 2, wherein said first clad layer is made of $\text{In}_{0.49}(\text{Ga}_{1-s}\text{Al}_s)_0.51\text{P}$ ($0.6 \leq s \leq 1$) and said second clad layer is made of $\text{In}_{0.49}(\text{Ga}_{1-y}\text{Al}_y)_0.51\text{P}$ ($0.4 \leq y \leq 0.75$, $y < s$).

5. The semiconductor light emitting device according to claim 4, wherein said window layer is made of $\text{Al}_v\text{Ga}_{1-v}\text{As}$ ($0.6 \leq v \leq 0.85$).

6. (currently amended): The semiconductor light emitting device according to claim

[[1,]] 2, wherein said first clad layer is made of $\text{Al}_z\text{Ga}_{1-z}\text{As}$ ($0.6 \leq z \leq 0.9$) and said second clad layer is made of $\text{Al}_u\text{Ga}_{1-u}\text{As}$ ($0.4 < u \leq 0.85$, $u < z$).

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7. (original): The semiconductor light emitting device according to claim 6, wherein said window layer is made of $\text{Al}_w\text{Ga}_{1-w}\text{As}$ ($0.4 \leq w < 0.7$, $w < u$).

8. (currently amended): ~~The semiconductor light emitting device according to claim 1;~~

A semiconductor light emitting device, comprising:

a semiconductor substrate;

a light emitting layer forming portion provided on said semiconductor substrate, in which an active layer made of a compound semiconductor is sandwiched between a first clad layer and a second clad layer made of compound semiconductor having band gap greater than that of said active layer, respectively and having a different conductivity type each other; and

a window layer provided at least above said second clad layer.

wherein said second clad layer is made of a compound semiconductor having a refractive index greater than that of said first clad layer provided on said semiconductor substrate side;

wherein a substrate side window layer is formed on said semiconductor substrate side of said first clad layer and said substrate side window layer is made of a material having a refractive index smaller than that of said first clad layer.

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